

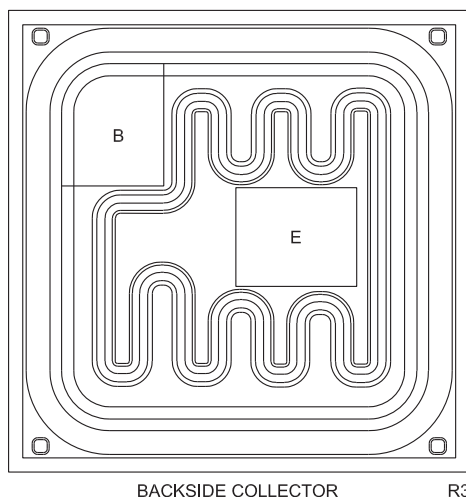
PROCESS CP191V
Small Signal Transistor
NPN - Amp/Switch Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
41,699

PRINCIPAL DEVICE TYPES

CMLT2222A
CMLT2207
CMLM2205
CMKT2207

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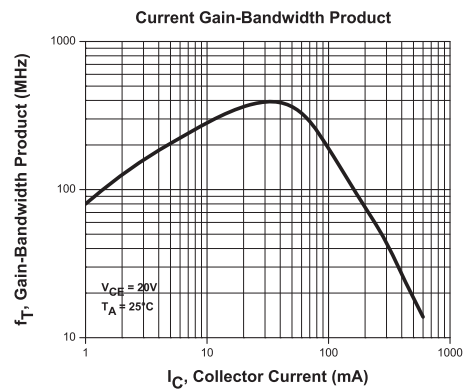
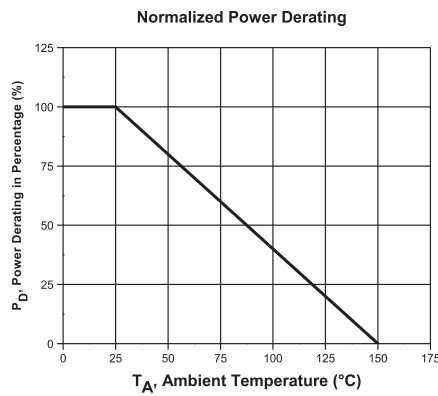
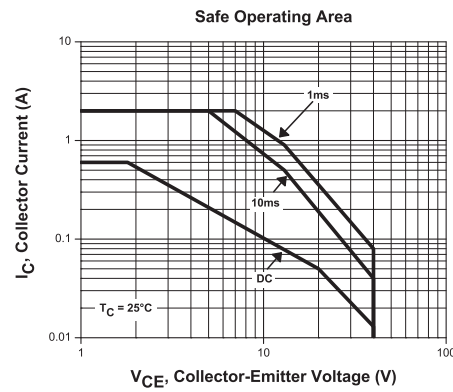
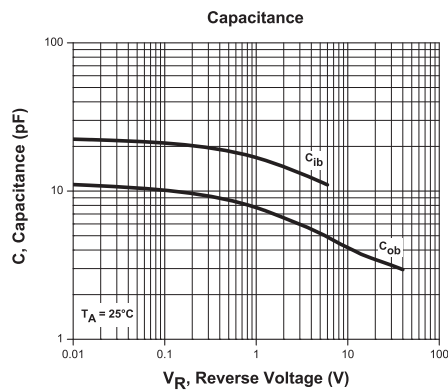
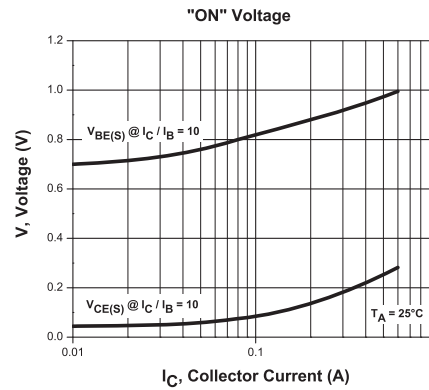
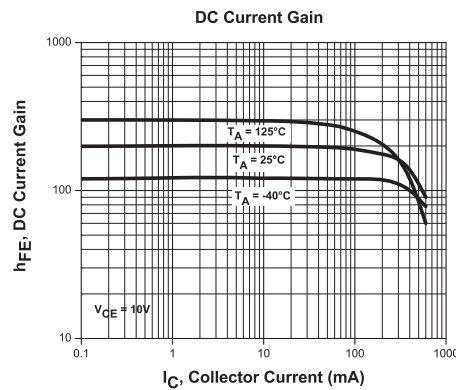
www.centrasemi.com

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PROCESS CP191V

Typical Electrical Characteristics



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